





LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

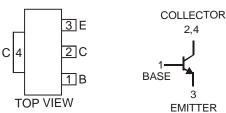
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DPLS350Y)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications

Lead Free By Design/RoHS Compliant (Note 1) "Green" Device (Note 2) SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	5	Α
Continuous Collector Current	Ic	3	Α
Base Current	I _B	0.5	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Cutoff Current	1	_	_	100	nA	$V_{CB} = 50V, I_{E} = 0$
	I _{CBO}		_	50	μΑ	$V_{CB} = 50V, I_E = 0, T_A = 150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	$V_{CE} = 50V, V_{BE} = 0$
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50	_	_	V	$I_C = 100 \mu A$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 100 \mu A$
ON CHARACTERISTICS (Note 4)						
		300	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
		300		_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h _{FE}	300	_	700	—	$V_{CE} = 2V$, $I_C = 1A$
		200		_		$V_{CE} = 2V$, $I_C = 2A$
		100	_	_		$V_{CE} = 2V$, $I_C = 3A$
	V _{CE(SAT)}	_	38	80		$I_C = 0.5A, I_B = 50mA$
			70	160	mV	$I_C = 1A$, $I_B = 50mA$
Collector-Emitter Saturation Voltage		_	130	280		$I_C = 2A$, $I_B = 100mA$
			124	260		$I_C = 2A$, $I_B = 200mA$
			180	370		$I_C = 3A$, $I_B = 300mA$
Equivalent On-Resistance	R _{CE(SAT)}		62	130	mΩ	$I_E = 2A$, $I_B = 200mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		_	1.1	V	$I_C = 2A$, $I_B = 100mA$
		_	_	1.2	V	$I_C = 3A$, $I_B = 300mA$
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	1.1	V	$V_{CE} = 2V$, $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	_	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	C_{obo}		_	25	pF	V _{CB} = 10V, f = 1MHz

4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

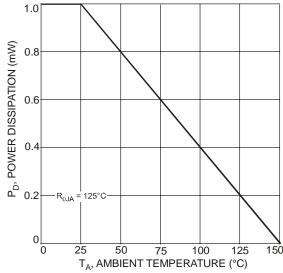


Fig. 1 Max Power Dissipation vs. Ambient Temperature

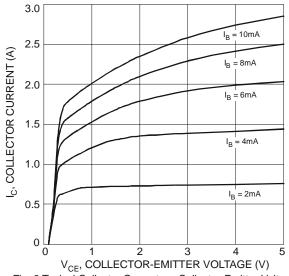
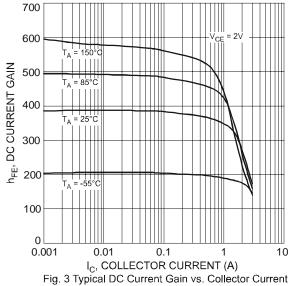


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage





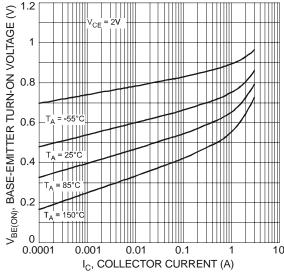


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

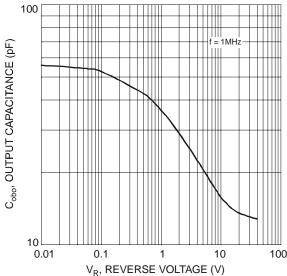


Fig. 7 Typical Output Capacitance Characteristics

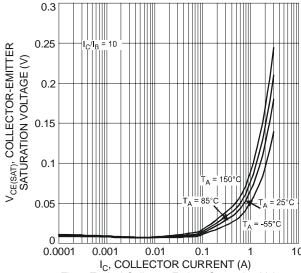


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

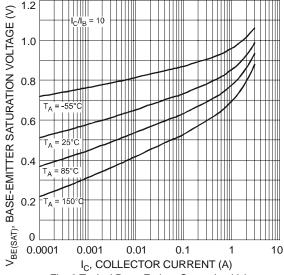
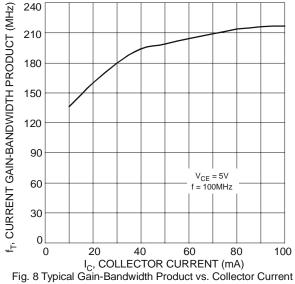


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



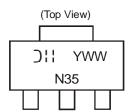


Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS350Y-13	SOT89-3L	2500/Tape & Reel

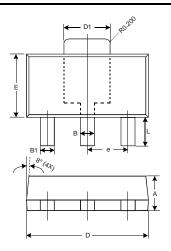
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

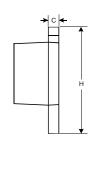
Marking Information



N35 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

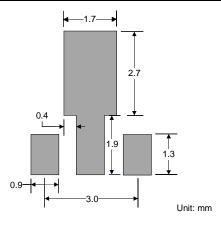
Package Outline Dimensions





SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
C	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е	_	_	1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					

Suggested Pad Layout



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